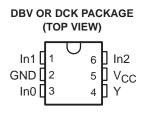
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- Available in the Texas Instruments NanoStar[™] and NanoFree[™] Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 6.3 ns at 3.3 V
- Low Power Consumption, 10-μA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

description/ordering information



YEA, YEP, YZA, OR YZP PACKAGE (BOTTOM VIEW)

In0	03	40	Y
GND	02	50	Vcc
ln1	01	60	ln2

This configurable multiple-function gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G58 features configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XOR, inverter, and noninverter. All inputs can be connected to V_{CC} or GND.

This device functions as an independent gate, but because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_{T-}) signals.

NanoStar[™] and NanoFree[™] package technology is a major breakthrough in IC packaging concepts, using the die as the package.

ORDERING INFORMATION

TA	PACKAGE [†]		ORDERABLE PART NUMBER	TOP-SIDE MARKING [‡]
	NanoStar™ – WCSP (DSBGA) 0.17-mm Small Bump – YEA		SN74LVC1G58YEAR	
	NanoFree™ – WCSP (DSBGA) 0.17-mm Small Bump – YZA (Pb-free)	Tape and reel	SN74LVC1G58YZAR	CD
–40°C to 85°C	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP		SN74LVC1G58YEPR	CP_
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC1G58YZPR	
	SOT (SOT-23) – DBV	Tape and reel	SN74LVC1G58DBVR	C58_
	SOT (SC-70) – DCK	Tape and reel	SN74LVC1G58DCKR	CP_

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

[‡]DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site.

YEA/YZA,YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition $(1 = \text{SnPb}, \bullet = \text{Pb-free})$.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoStar and NanoFree are trademarks of Texas Instruments.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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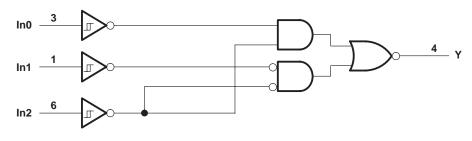
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description/ordering information (continued)

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE							
	INPUTS	OUTPUT					
In2	In1	In0	Y				
L	L	L	L				
L	L	Н	н				
L	Н	L	L				
L	Н	Н	н				
н	L	L	н				
н	L	Н	н				
н	Н	L	L				
Н	Н	Н	L				

logic diagram (positive logic)





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FUNCTION SELECTION TABLE					
LOGIC FUNCTION	FIGURE NO.				
2-input AND with inverted input	2, 3				
2-input NAND	1				
2-input NAND with both inputs inverted	4				
2-input OR	4				
2-input OR with both inputs inverted	1				
2-input NOR with inverted input	2, 3				
2-input XOR	5				

FUNCTION SELECTION TABLE

logic configurations

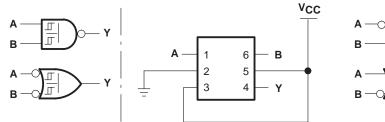


Figure 1. 2-Input NAND Gate

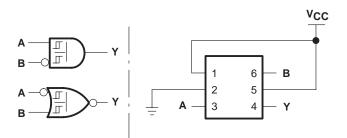
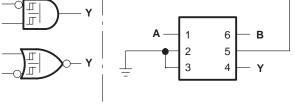


Figure 3. 2-Input AND Gate With Inverted B Input



Vcc

Figure 2. 2-Input AND Gate With Inverted A Input

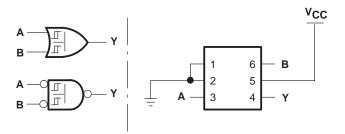


Figure 4. 2-Input OR Gate

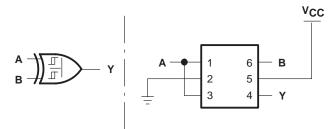


Figure 5. 2-Input XOR Gate



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC} Input voltage range, V _I (see Note 1) Voltage range applied to any output in the high-impedance or power-off state, V _O	
(see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V _O	
(see Notes 1 and 2)	–0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, I _O	
Continuous current through V _{CC} or GND	
Package thermal impedance, θ_{JA} (see Note 3): DBV package	
DCK package	
YEA/YZA package	143°C/W
YEP/YZP package	
Storage temperature range, T _{stg}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The value of V_{CC} is provided in the recommended operating conditions table.

3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
Vaa	Supply voltage	Operating	1.65	5.5	V	
Vcc	Supply voltage	Data retention only			v	
VI	Input voltage		0	5.5	V	
VO	Output voltage		0	VCC	V	
		V _{CC} = 1.65 V		-4		
I _{OH} Hig	High-level output current	$V_{CC} = 2.3 V$		-8		
				-16	mA	
		V _{CC} = 3 V		-24		
		$V_{CC} = 4.5 V$		-32		
		V _{CC} = 1.65 V		4		
		$V_{CC} = 2.3 V$		8		
IOL	Low-level output current			16	mA	
		V _{CC} = 3 V		24		
		$V_{CC} = 4.5 V$		32		
Τ _Α	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



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			V _{CC}		ΤΥΡ [†] ΜΑΧ	UNIT
V _{T+}			1.65 V	0.79	1.16	
			2.3 V	1.11	1.56	
Positive-going input threshold			3 V	1.5	1.87	V
voltage			4.5 V	2.16	2.74	
			5.5 V	2.61	3.33	
			1.65 V	0.39	0.62	
VT-			2.3 V	0.58	0.87	
Negative-going input threshold			3 V	0.84	1.14	V
voltage			4.5 V	1.41	1.79	
			5.5 V	1.87	2.29	
			1.65 V	0.37	0.62	
ΔV_T			2.3 V	0.48	0.77	
Hysteresis			3 V	0.56	0.87	V
$(V_{T+} - V_{T-})$			4.5 V	0.71	1.04	
			5.5 V	0.71	1.11	
	I _{OH} = -100 μA		1.65 V to 5.5 V	V _{CC} -0.1		
	$I_{OH} = -4 \text{ mA}$		1.65 V	1.2		
	I _{OH} =8 mA		2.3 V	1.9		.,
VOH	I _{OH} = -16 mA		3 V	2.4		V
	I _{OH} = -24 mA		3 V	2.3		
	I _{OH} = -32 mA		4.5 V	3.8		
	I _{OL} = 100 μA		1.65 V to 5.5 V		0.1	
	I _{OL} = 4 mA		1.65 V		0.45	
	I _{OL} = 8 mA		2.3 V		0.3	
VOL	I _{OL} = 16 mA				0.4	V
	I _{OL} = 24 mA		3 V		0.55	
	I _{OL} = 32 mA		4.5 V		0.55	
lı	V _I = 5.5 V or GND		0 to 5.5 V		±1	μΑ
l _{off}	$V_{\rm I}$ or $V_{\rm O}$ = 5.5 V		0		±10	μA
ICC	$V_{\rm I} = 5.5 \text{ V or GND},$	I _O = 0	1.65 V to 5.5 V		10	μA
100						
	One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 5.5 V		500	μA

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} = ± 0.2		V _{CC} = ± 0.3		۲ <mark>۰۵</mark> کا ± ۵.		UNIT
		(001101)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	Any In	Y	3.2	14.4	2	8.3	1.5	6.3	1.1	5.1	ns



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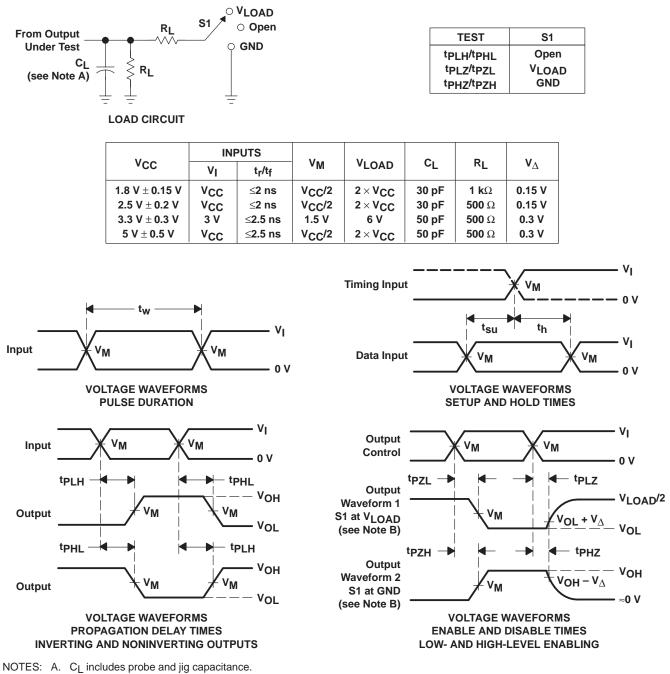
operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
		CONDITIONS	TYP	TYP	TYP	TYP	UNIT
Cpd	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF

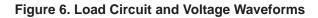


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PARAMETER MEASUREMENT INFORMATION



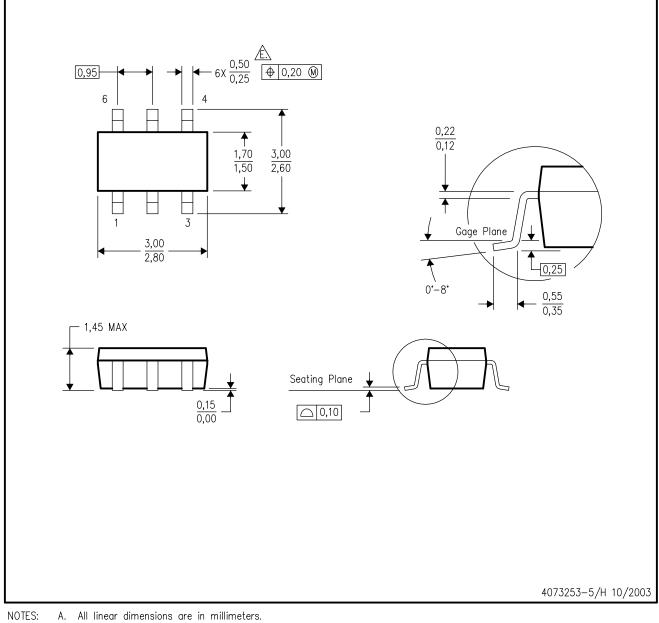
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_Q = 50 Ω .
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tPLH and tPHL are the same as tpd.
- H. All parameters and waveforms are not applicable to all devices.





DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



- Β. This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusion.
- C. D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- E Falls within JEDEC MO-178 Variation AB, except minimum lead width.

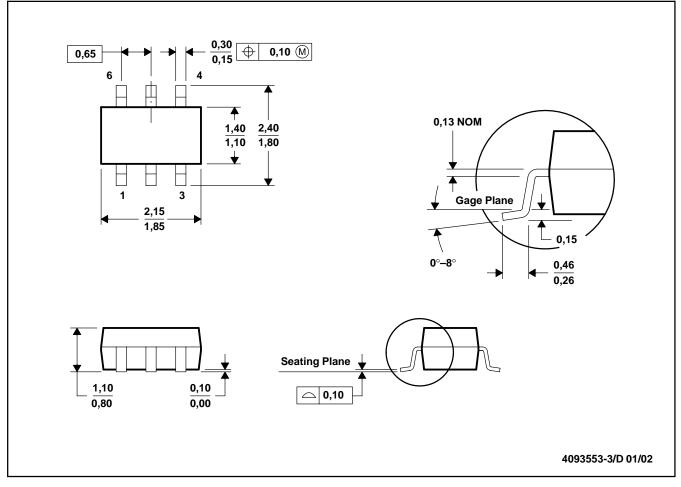


MECHANICAL DATA

MPDS114 - FEBRUARY 2002

DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



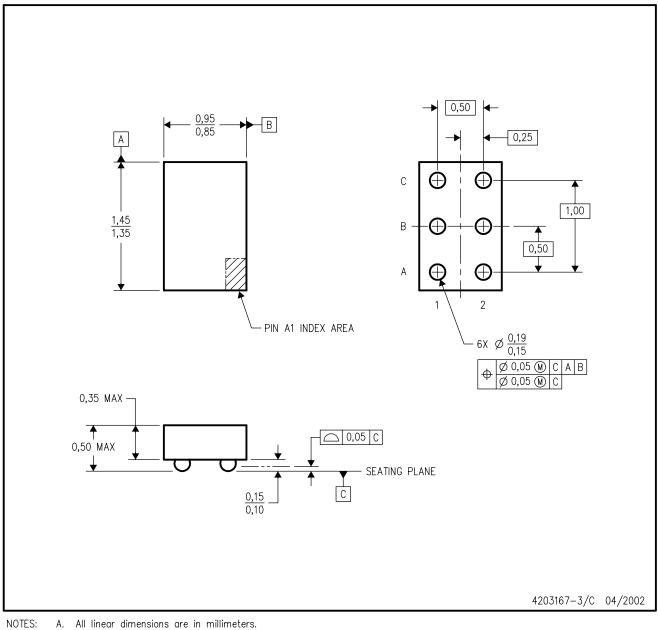
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-203



YEA (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



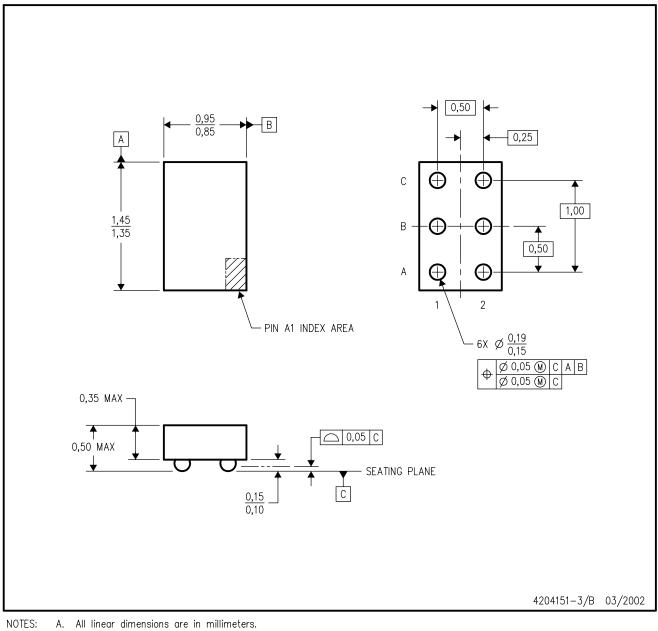
- B. This drawing is subject to change without notice.
- C. NanoStar™ package configuration.
- D. Package complies to JEDEC MO-211 variation EA.
- E. This package is tin-lead (SnPb). Refer to the 6 YZA package (drawing 4204151) for lead-free.

NanoStar is a trademark of Texas Instruments.



YZA (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



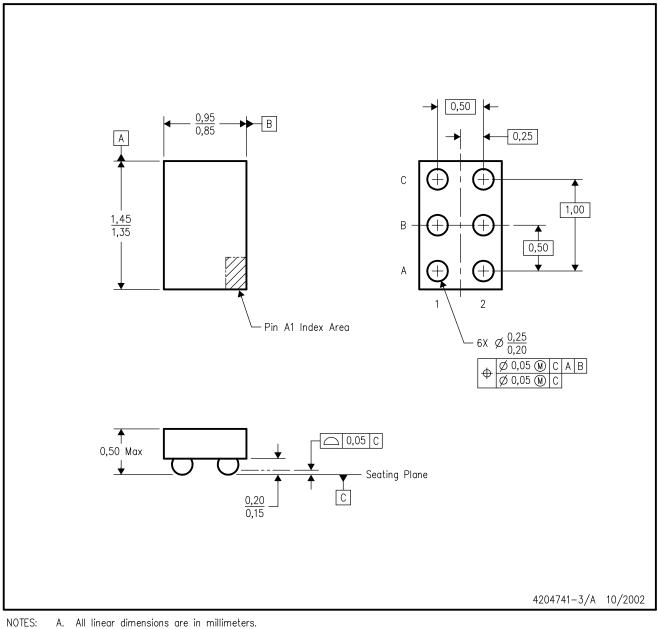
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. Package complies to JEDEC MO-211 variation EA.
- E. This package is lead-free. Refer to the 6 YEA package (drawing 4203167) for tin-lead (SnPb).

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YZP (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



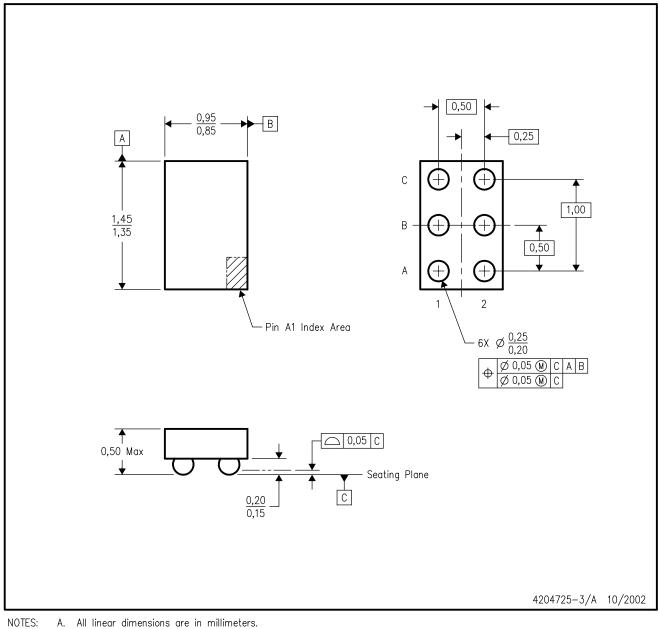
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. This package is lead-free. Refer to the 6 YEP package (drawing 4204725) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



YEP (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



- B. This drawing is subject to change without notice.
- C. NanoStar™ package configuration.
- D. This package is tin-lead (SnPb). Refer to the 6 YZP package (drawing 4204741) for lead-free.

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